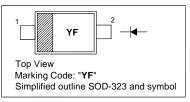
SILICON SCHOTTKY BARRIER DIODE

Features

- Low forward voltage drop and suitable for high effifiency rectifying
- Ultra small resin package is suitable for high density surface mounting and high speed assembly

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Mean Rectifying Current	Io	100	mA
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine Wave)	I _{FSM}	1	Α
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V_{F}	0.44	V
Reverse Current at $V_R = 30 \text{ V}$	I _R	50	μA





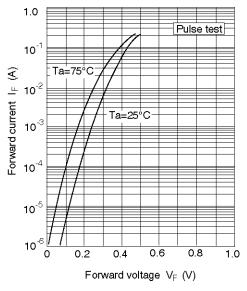


Fig.1 Forward current Vs. Forward voltage

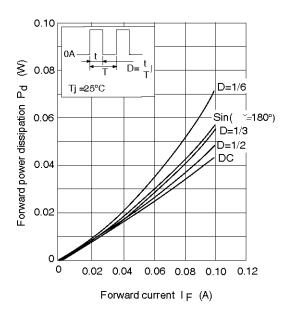


Fig.3 Forward power dissipation Vs. Forward current

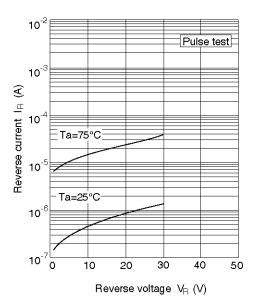


Fig.2 Reverse current Vs. Reverse voltage

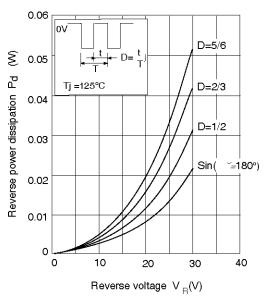


Fig.4 Reverse power dissipation Vs. Reverse voltage



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

